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JAN 24 2006

SCULLY, SCOTT, MURPHY
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To:	Examiner Fernando L. Toledo Art Unit: 2823	From:	Leslie S. Szivos
Fax:	571-273-8300	Pages:	12 pages (including fax cover)
Phone:		Date:	January 24, 2006
Re:	Hussein I. Hanafi et al. U.S. Patent Appln. No. 10/659,949 Docket: YOR920020182US2 (15790A) Conf. No.: 5877	CC:	

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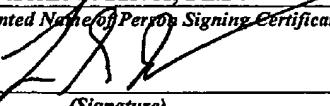
1. Transmittal of Response Under 37 C.F.R. 1.111 (in duplicate)
2. Response Under 37 C.F.R. 1.111 (7 pages)
3. Certificate of transmission by facsimile dated January 24, 2006
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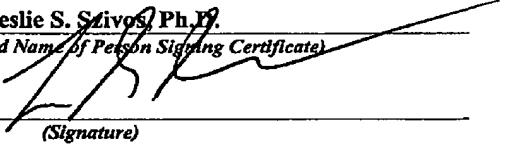
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JAN 24 2006

CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)			Docket No. YOR920020182US2 (15790A)
Applicant(s): Hussein I. Hanafi et al.			
Application No. 10/659,949	Filing Date September 11, 2003	Examiner Fernando L. Toledo	Group Art Unit 2823
Invention: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE REMOVAL ETCH			
<p>I hereby certify that this <u>Response under 37 C.F.R. §§1.111</u> <small>(Identify type of correspondence)</small></p> <p>is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. <u>571-273-8300</u>)</p> <p>on <u>January 24, 2006</u> <small>(Date)</small></p> <p style="text-align: right;"><u>Leslie S. Szivos, Ph.D.</u> <small>(Typed or Printed Name of Person Signing Certificate)</small></p> <p style="text-align: right;"> <small>(Signature)</small></p> <p>Note: Each paper must have its own certificate of mailing.</p>			

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JAN 24 2006

AMENDMENT TRANSMITTAL LETTER (Large Entity) Applicant(s): Hussein I. Hanafi et al.				Docket No. YOR920020182US2 (15790A)	
Application No. 10/659,949	Filing Date September 11, 2003	Examiner Fernando L. Toledo	Customer No. 23389	Group Art Unit 2823	Confirmation No. 5877
Invention: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE REMOVAL ETHCH					
<u>COMMISSIONER FOR PATENTS:</u>					
Transmitted herewith is an amendment in the above-identified application.					
The fee has been calculated and is transmitted as shown below.					
CLAIMS AS AMENDED					
	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST # PREV. PAID FOR	NUMBER EXTRA CLAIMS PRESENT	RATE	ADDITIONAL FEE
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INDEP. CLAIMS	3 -	3 =	0	x	\$0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					\$0.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0.00
<p><input checked="" type="checkbox"/> No additional fee is required for amendment.</p> <p><input type="checkbox"/> Please charge Deposit Account No. in the amount of</p> <p><input type="checkbox"/> A check in the amount of to cover the filing fee is enclosed.</p> <p><input checked="" type="checkbox"/> The Director is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account 50-0510/IBM</p> <p><input checked="" type="checkbox"/> Any additional filing fees required under 37 C.F.R. 1.16.</p> <p><input checked="" type="checkbox"/> Any patent application processing fees under 37 CFR 1.17.</p> <p><input checked="" type="checkbox"/> Payment by credit card. Form PTO-2038.</p>					
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<i>Typed or Printed Name of Person Mailing Correspondence</i>					

JAN 24 2006

AMENDMENT TRANSMITTAL LETTER (Large Entity)

Applicant(s): Hussein I. Hanafi et al.

Docket No.

YOR920020182US2 (15790A)

Application No. 10/659,949	Filing Date September 11, 2003	Examiner Fernando L. Toledo	Customer No. 23389	Group Art Unit 2823	Confirmation No. 5877
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Invention: **LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE REMOVAL ETHCH**COMMISSIONER FOR PATENTS:

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The fee has been calculated and is transmitted as shown below.

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TOTAL CLAIMS	9 -	20 =	0	x	\$0.00
INDEP. CLAIMS	3 -	3 =	0	x	\$0.00
Multiple Dependent Claims (check if applicable)		<input type="checkbox"/>			\$0.00
					TOTAL ADDITIONAL FEE FOR THIS AMENDMENT
					\$0.00

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Dated: January 24, 2006

Leslie S. Szivos, Ph.D.
Registration No. 39,394

LSS:vh
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:	Hussein I. Hanafi et al.	
Serial No.:	10/659,949	
Filed:	September 11, 2003	
For:	LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE REMOVAL ETCH	
Docket:	YOR920020182US2 (15790A)	
Examiner:	Fernando L. Toldeo	
Art Unit:	2823	
Dated:	January 24, 2006	
Confirmation No:	5877	

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

RESPONSE UNDER 37 C.F.R. § 1.111

Sir:

In response to the Office Action dated October 31, 2005, applicants submit the following amendments and remarks for entry of record in the above-identified patent application.

CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that this paper is being facsimile transmitted to the Patent and Trademark Office on the date shown below.

Dated: January 24, 2006


Leslie S. Szivos